1. General description

PNP high-voltage low V_{CEsat} transistor in a SOT89 (SC-62) medium power and flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBHV8540X

2. Features and benefits

- · High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain h_{FE} at high I_C

3. Applications

- Electronic ballast for fluorescent lighting
- LED driver for LED chain module
- LCD backlighting
- High Intensity Discharge (HID) front lighting
- · Hook switch for wired telecom
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-400	V
I _C	collector current		-	-	-0.5	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms	-	-	-1	Α
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -20 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	140	-	450	
R _{CEsat}	collector-emitter saturation resistance	I_C = -200 mA; I_B = -40 mA; pulsed; t_p = 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	2000	mΩ



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1	B—[
			SOT89	sym132

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV9540X		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBHV9540X	%4Н

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

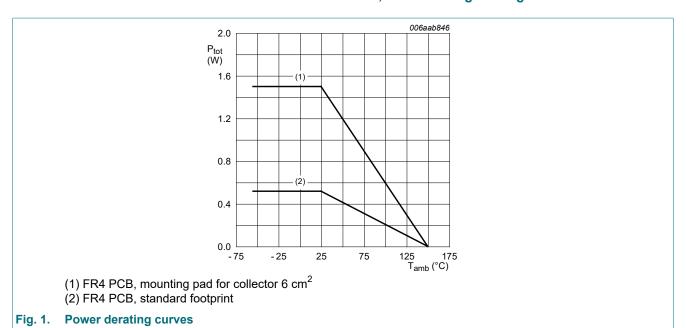
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	-400	V
V _{CEO}	collector-emitter voltage	open base		-	-400	V
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V		-	-400	V
V _{EBO}	emitter-base voltage	open collector		-	-7	V
I _C	collector current			-	-0.5	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-1	Α
I _B	base current			-	-250	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.52	W
			[2]	-	1.5	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

PBHV9540X

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1]	-	-	240	K/W
junction to ambient	junction to ambient		[2]	-	-	83	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	20	-	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

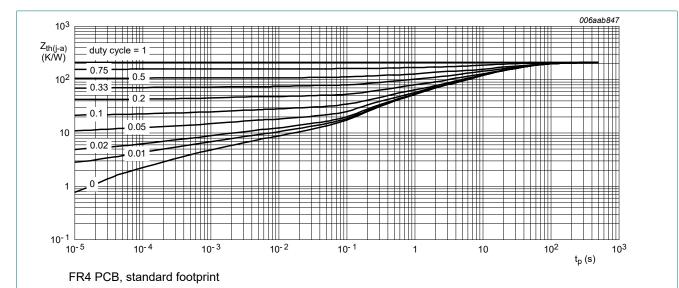


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

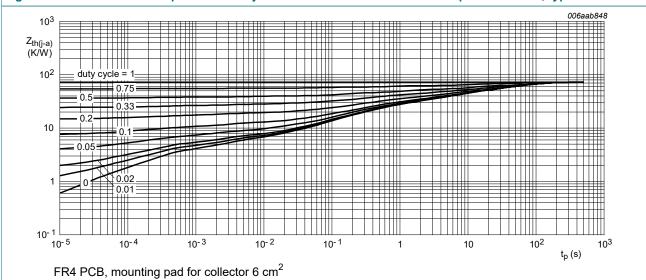


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

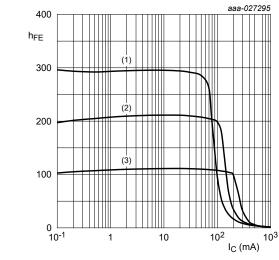
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = -100 \ \mu A; I_C = 0 \ A; T_{amb} = 25 \ ^{\circ}C$	-7	-	-	V
I _{CBO}	collector-base cut-off	$V_{CB} = -320 \text{ V}; I_{E} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-	-	-100	nA
	current	V _{CB} = -320 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = -320 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	-100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = -7 V; I _C = 0 A; T _{amb} = 25 °C	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -5 V; I _C = -20 mA; T _{amb} = 25 °C	140	-	450	
		V_{CE} = -5 V; I_{C} = -100 mA; pulsed; $t_{p} \le$ 300 μs; $δ \le$ 0.02; T_{amb} = 25 °C	140	-	400	
V _{CEsat}	collector-emitter saturation voltage	I_C = -100 mA; I_B = -20 mA; pulsed; $t_p \le$ 300 μs; $δ \le 0.02$; T_{amb} = 25 °C	-	-	-250	mV
		I_C = -200 mA; I_B = -40 mA; pulsed; $t_p \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	-400	mV
R _{CEsat}	collector-emitter saturation resistance	I_C = -200 mA; I_B = -40 mA; pulsed; t_p = 300 μs; δ ≤ 0.02; T_{amb} = 25 °C	-	-	2000	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = -100 mA; I_B = -10 mA; pulsed; $t_p \le$ 300 μs; $δ \le 0.02$; T_{amb} = 25 °C	-	-	-0.9	V
		I_C = -200 mA; I_B = -40 mA; pulsed; $t_p \le$ 300 μs; $\delta \le$ 0.02; T_{amb} = 25 °C	-	-	-1	V
V_{BE}	base-emitter voltage	V_{CE} = -10 V; I_{C} = -200 mA; pulsed; $t_{p} \le$ 300 μs; $δ \le$ 0.02; T_{amb} = 25 °C	-	-	-0.9	V
t _d	delay time	V _{CC} = -6.2 V; I _C = -100 mA;	-	60	-	ns
t _r	rise time	I_{Bon} = -10 mA; I_{Boff} = 20 mA; T_{amb} = 25 °C	-	3650	-	ns
t _{on}	turn-on time	1 amb = 23 0	-	3710	-	ns
t _s	storage time		-	810	-	ns
t _f	fall time		-	900	-	ns
t _{off}	turn-off time		-	1710	-	ns
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -50 mA; f = 100 MHz; T_{amb} = 25 °C	-	65	-	MHz
C _c	collector capacitance	V _{CB} = -10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	14	-	pF
C _e	emitter capacitance	V _{EB} = -0.5 V; I _C = 0 A; i _c = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	235	-	pF

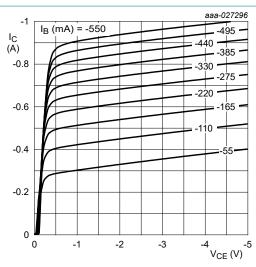
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$$V_{CE} = -5 \text{ V}$$

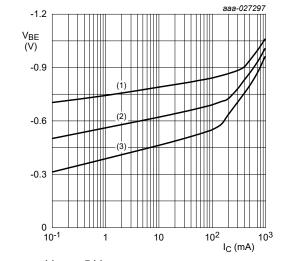
(2)
$$I_{amb} = 25 ^{\circ} C$$

Fig. 4. DC current gain as a function of collector current; typical values



 T_{amb} = 25 °C

Fig. 5. Collector current as a function of collectoremitter voltage; typical values



$$V_{CE}$$
 = -5 V

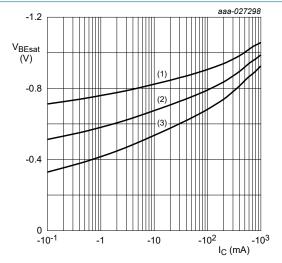
$$(1) T_{amb} = -55 ° C$$

(1)
$$T_{amb} = -55 \,^{\circ}C$$

(2) $T_{amb} = 25 \,^{\circ}C$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 6. Base-emitter voltage as a function of collector current; typical values



$$I_C/I_B = 5$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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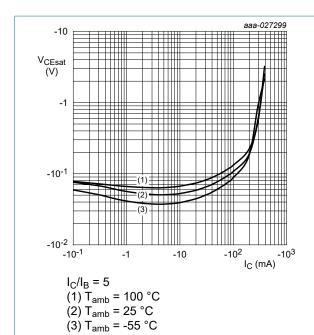


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

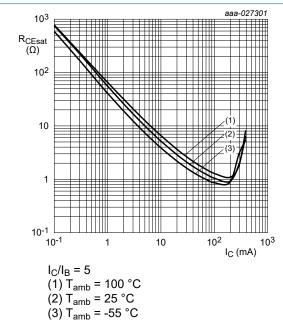


Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

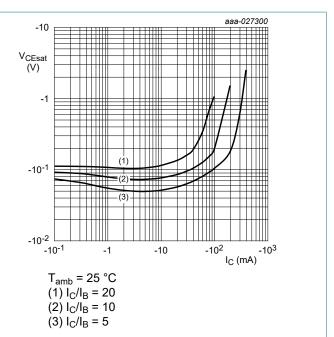


Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values

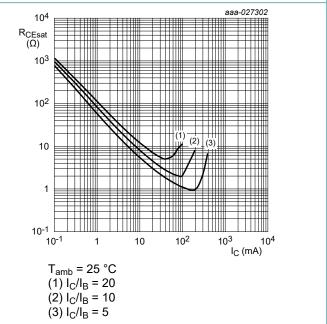
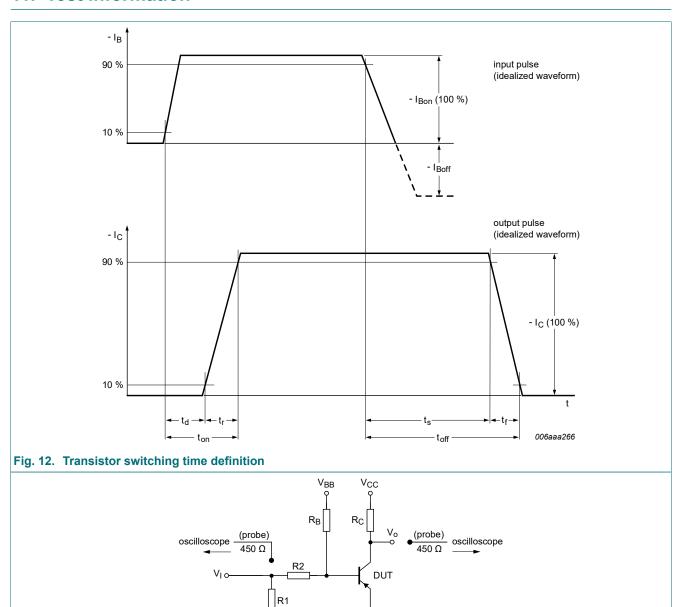


Fig. 11. Collector-emitter saturation resistance as a function of collector current; typical values

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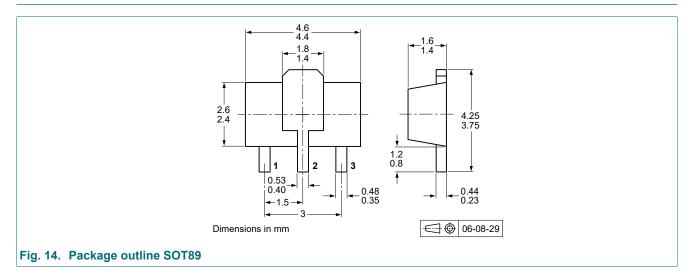
11. Test information



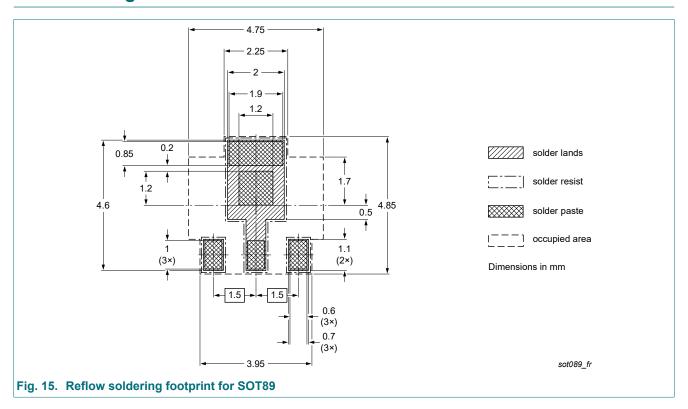
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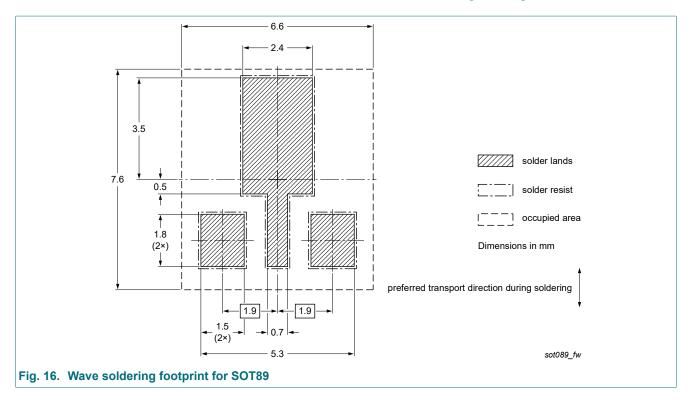
12. Package outline



13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PBHV9540X v.2	20241009	Product data sheet	-	PBHV9540X v.1				
Modifications:		Product(s) changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s).						
PBHV9540X v.1	20170928	Product data sheet	-	-				

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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